

# **isc Silicon NPN Power Transistor**

# 2SD1718

#### **DESCRIPTION**

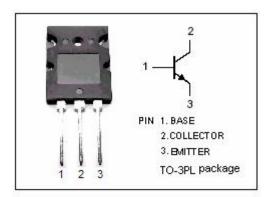
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 180V(Min.)
- · Good Linearity of hFE
- · Wide Area of Safe Operation
- Complement to Type 2SB1163
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

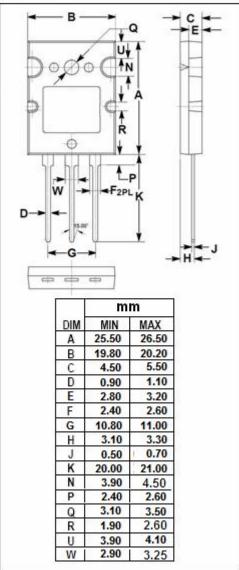


· Designed for high power amplifier applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
Vсво	Collector-Base Voltage	170	V	
V <sub>CEO</sub>	Collector-Emitter Voltage 170		V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
lc	Collector Current-Continuous 15		А	
I <sub>CP</sub>	Collector Current-Pulse 25		А	
P <sub>C</sub>	Collector Power Dissipation @ $T_C$ =25 $^{\circ}$ C	150	W	
	Collector Power Dissipation @ T <sub>a</sub> =25 ℃	3.5		
Тл	Junction Temperature 150		°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	







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### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			2.5	V
V <sub>BE(on)</sub>	Base -Emitter On Voltage	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V			1.8	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 170V; I <sub>E</sub> = 0			50	μА
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 3V; I <sub>C</sub> = 0			50	μА
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 20mA; V <sub>CE</sub> = 5V	20			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	60		200	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 8A; V <sub>CE</sub> = 5V	20			
Сов	Collector Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		230		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V		20		MHz

#### ♦ h<sub>FE-2</sub> Classifications

Q	S	Р
60-120	80-160	100-200

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